

BCR10PM-12LG

Triac

Medium Power Use

REJ03G1509-0100 Rev.1.00 Feb 14, 2007

Features

 $\bullet \quad I_{FGTI},\,I_{RGTI},\,I_{RGT\,III}\!\!:30\;mA$

• V_{iso}: 2000 V

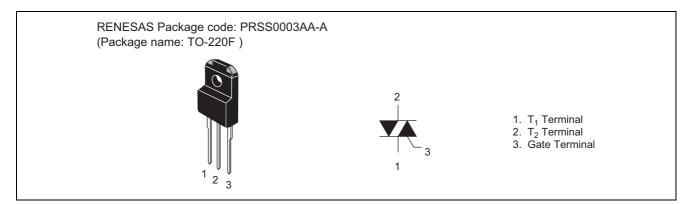
• The Product guaranteed maximum junction temperature 150°C

• Insulated Type

Planar Type

UL Recognized : Yellow Card No. E223904
 File No.E80271

Outline



Applications

Switching mode power supply, light dimmer, electronic switch, hair dryer, Television, Stereo system, refrigerator, Washing machine, infrared kotatsu, and carper, small motor controller, SS relay, solenoid driver, copying machine, electric tool, electric heater control, and other general purpose control applications

Parameter	Symbol	Voltage class	Unit	
Farameter	Symbol	12	Onit	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V	
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V	



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Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	10	А	Commercial frequency, sine full wave 360°conduction, Tc = 103°C
Surge on-state current	I _{TSM}	100	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusion	l ² t	41.6	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I _{GM}	2	Α	
Junction Temperature	Tj	-40 to +150	°C	
Storage temperature	Tstg	-40 to +150	°C	
Mass	_	2.0	g	Typical value
Isolation voltage	V _{iso}	2000	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

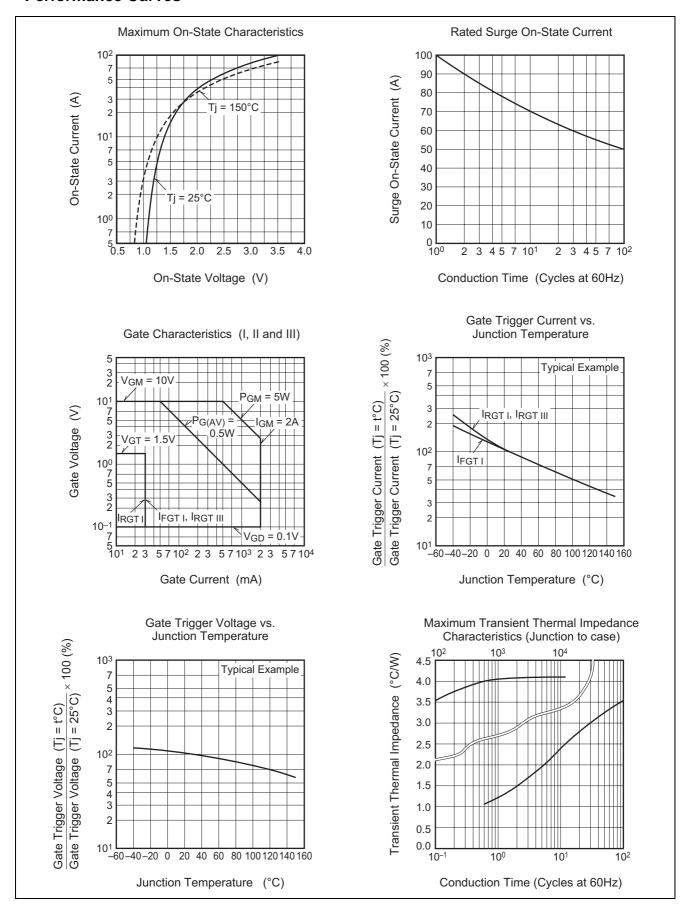
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state		I _{DRM}	_	_	2.0	mA	Tj = 150°C, V _{DRM} applied
current							
On-state voltage		V_{TM}	_	_	1.5	V	$Tc = 25^{\circ}C, I_{TM} = 15 A,$
							instantaneous measurement
Gate trigger voltage ^{Note2}	I	$V_{FGT_{I}}$		_	1.5	V	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	V_{RGTI}	_	_	1.5	V	$R_G = 330 \Omega$
	III	V_{RGTIII}	_	_	1.5	V	
Gate trigger curent ^{Note2}	I	I _{FGTI}	_	_	30	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	I_{RGTI}	_	_	30	mA	$R_G = 330 \Omega$
	III	I _{RGTIII}	_	_	30	mA	
Gate non-trigger voltage		V_{GD}	0.2/0.1	_	_	V	$Tj = 125$ °C/150°C, $V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	_	_	4.1	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-state		(dv/dt)c	10/1	_	_	V/μs	Tj = 125°C/150°C
commutation voltage ^{Note4}							

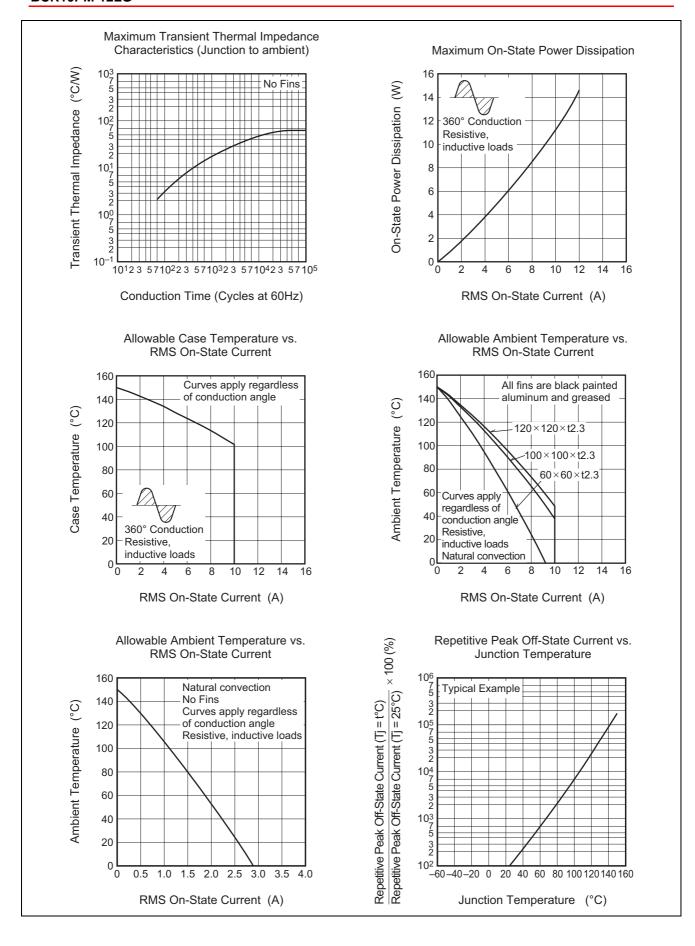
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

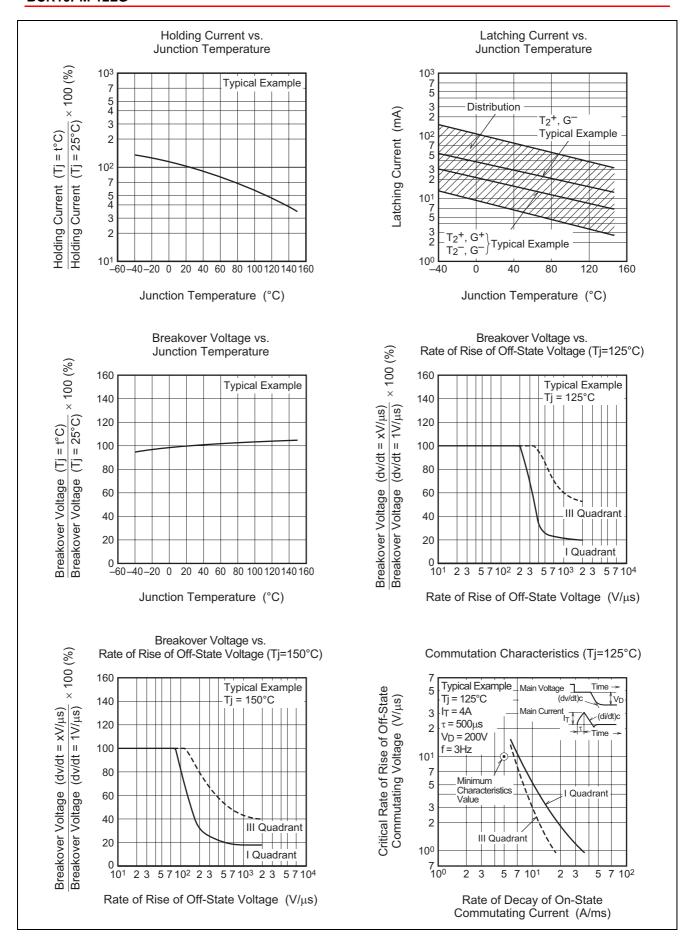
- 3. The contact thermal resistance $R_{th\;(j\text{-}c)}$ in case of greasing is $0.5^{\circ}\text{C/W}.$
- 4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

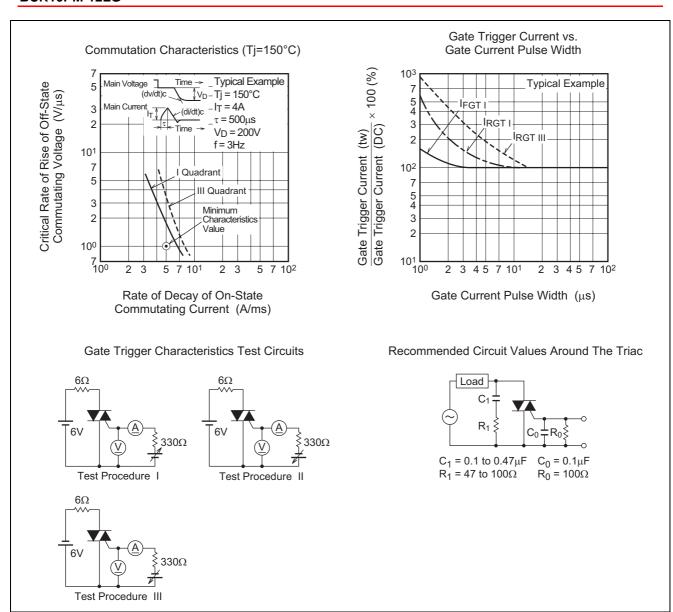
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C/150°C	Supply Voltage
2. Rate of decay of on-state commutating current (di/dt)c = −5.0 A/ms	Main Current ————————————————————————————————————
3. Peak off-state voltage V _D = 400 V	Main Voltage — Time (dv/dt)c

Performance Curves

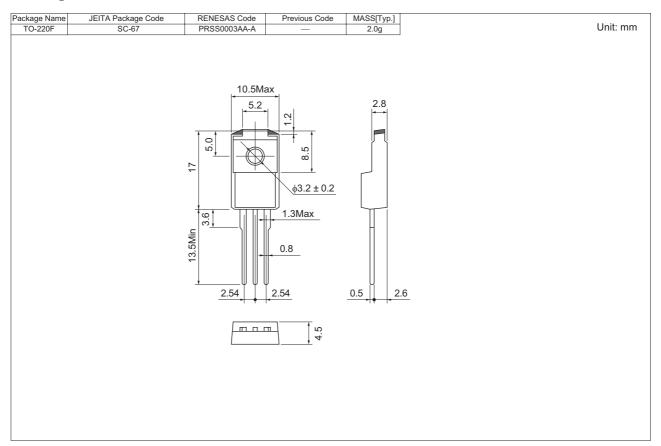








Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR10PM-12LG
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR10PM-12LG-A8

Note: Please confirm the specification about the shipping in detail.

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